



74LVC2T45

DUAL BIT DUAL POWER SUPPLY TRANSLATING TRANSCEIVER WITH 3 STATE OUTPUTS

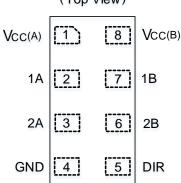
Description

The 74LVC2T45 is a dual-bit, dual-supply transceiver with tri-state outputs suitable for transmitting two logic bits across different voltage domains. The direction pin (DIR) and Port A, consisting of pins 1A and 2A, have logic levels in relation to $V_{\rm CC}(A)$ while port B, consisting of pins 1B and 2B have logic levels related to $V_{\rm CC}(B)$. This arrange- ment allows for universal low-voltage translation between any voltages from 1.2V to 5.5V. When a HIGH logic level is applied to the direction pin, port A pins become inputs and port B pins are outputs. Conversely, the roles of the ports are reversed when the direction pin is asserted LOW.

The tri-state (loff) feature places all port pins in a high impedance state when either power supply is at 0V, which prevents and damages backflow currents and provides power-down electrical isolation up to 5.5V as not to interfere with any logic activity on either of the ports.

(Top View)

Pin Assignments



X2-DFN1210-8 X2-DFN1410-8

Features

- Wide Supply Voltage Range:
 - Vcc(A): from 1.2V to 5.5V
 - Vcc(B): from 1.2V to 5.5V
- ± 24mA Output Drive at 3.3V
- CMOS Low Power Consumption 16µA Maximum Icc
- · High Noise Immunity
- IOFF Supports Partial-Power-Down Mode Operation
- Ioff Controlled by Either Vcc Being at 0V
- Inputs Accept up to 5.5V
- Maximum data rates:
 - 420Mbps (3.3V to 5V translation)
 - 210Mbps (translate to 3.3V)
 - 140Mbps (translate to 2.5V)
 - 75Mbps (translate to 1.8V)
 - 60Mbps (translate to 1.5V)
- ESD Protection Exceeds JESD 22
 - 4000-V Human Body Model (A114)
 - 1000 V Charged Device Model (C101)
- Latch-up Exceeds 100mA per JESD 78, Class I
- Specified from -40°C to +85°C and -40°C to +125°C
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Applications

- Voltage Level Translation
 Well-Suited to Join Logic Types Operating at Different Voltages
- Power-Down Signal Isolation
 If Either Voltage Domain is Turned Off the Signal is Isolated and
 There is No Loading on Signal Lines
- Wide Array of Products, such as:
 - Cell Phones, Tablets, E-Readers
 - PCs, Notebooks, Netbooks, Ultrabooks
 - Networking, Routers, Gateways
 - Computer Peripherals, Hard Drives, CD/DVD ROM
 - TV, DVD, DVR, Set-Top Box
 - Personal Navigation / GPS
 - MP3 Players, Cameras, Video Recorders

Notes:

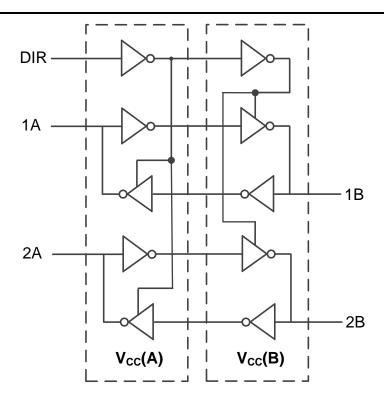
- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



Pin Descriptions

Pin Name	Pin	Function	
VCC(A)	1	Supply for I/O Pin A; Reference for DIR	
1A	2	Data Input/Output	
2A	3	Data Input/Output	
GND	4	Ground	
DIR	5	Direction Control	
2B	6	Data Input/Output	
1B	7	Data Input/Output	
VCC(B)	8	Supply for I/O Pin B	

Logic Diagram



Function Tables

Input DIR (Direction Pin)	Operation				
L	B Data to A Output				
Н	A Data to B Output				

	Inputs		Outputs			
Α	B DIR		Α	В		
Note 4	L	L	L	Note 4		
Note 4	Н	L	Н	Note 4		
L	Note 4	Н	Note 4	L		
Н	Note 4	Н	Note 4	Н		

Note: 4. Pin condition not applicable as defined by DIR.



Absolute Maximum Ratings (Note 5) (@TA = +25°C, unless otherwise specified.)

Symbol	Parameter		Rating	Unit			
ESD HBM	Human Body Model ESD Protection		4	KV			
ESD CDM	Charged Device Model ESD Protection		1	KV			
Vcc(A), Vcc(B)	Supply Voltage Range		-0.5 to +6.5	V			
Vı	Input Voltage Range						
Vo	Voltage Applied to Output in High Impedance or Ioff	-0.5 to +6.5	V				
1/	Voltage Applied to Output in High or Low State	A Pin	-0.3 to V _{CC} (A) +0.5	V			
Vo	Voltage Applied to Output in High or Low State	B Pin	-0.3 to Vcc(B) +0.5	V			
lıĸ	Input Clamp Current V _I < 0		-50	mA			
Іок	Output Clamp Current		-50	mA			
lo	Continuous Output Current		±50	mA			
_	Continuous Current Through Vcc or GND	±100	mA				
TJ	Operating Junction Temperature	-40 to +150	°C				
Tstg	Storage Temperature		-65 to +150	°C			

Note:

Recommended Operating Conditions (Note 6) (@T_A = +25°C, unless otherwise specified.)

Symbol	Parameter	Conditions	Min	Max	Unit
Vcc(A)	Supply Voltage A	_	1.2	5.5	V
Vcc(B)	Supply Voltage B	_	1.2	5.5	V
Vı	Input Voltage	_	0	5.5	V
.,	Output Valta va	Active Mode (Note 6)	0	V _{cco}	V
Vo	Output Voltage	Suspend or 3-State Mode	0	5.5	V
T _A	Ambient Temperature	_	-40	+125	°C
		V _{CCI} = 1.2V (Note 7)	_	20	ns/V
		V _{CCI} = 1.4V to 1.95V	_	20	ns/V
Δt/ΔV	Input Transition Rise and Fall Rate	Vcci = 2.3V to 2.7V	_	20	ns/V
		Vcci = 3V to 3.6V	_	10	ns/V
		V _{CCI} = 4.5V to 5.5V	_	5	ns/V

Notes:

^{5.} Stresses beyond the absolute maximum can result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

^{6.} V_{CCO} is the supply voltage associated with the output port.

^{7.} V_{CCI} is the supply voltage associated with the input port.



Electrical Characteristics (@TA = +25°C.)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{OH}	HIGH-Level Output Voltage	$V_I = V_{IH}$ or V_{IL} ; $I_O = -3mA$; $V_{CCO} = 1.2V$	1	1.09		٧
V_{OL}	LOW-Level Output Voltage	VI = VIH or VIL; IO = 3mA; VCCO = 1.2V	ı	0.07		٧
lı	Input Leakage Current	DIR Input; $V_1 = 0V$ to 5.5V; $V_{CCI} = 1.2V$ to 5.5V	1	_	±1	μΑ
I _{OZ}	OFF-State Output Current	A or B Port; Vo = 0 V or Vcco; Vcco = 1.2V to 5.5V	1	_	±1	μΑ
_	Dower Off Lookage Current	A Port; V _I or V _O = 0 V to 5.5 V; V _{CC} (A) = 0 V; V _{CC} (B) = 1.2V to 5.5V	1	_	±1	μΑ
l _{OFF}	Power-Off Leakage Current	B Port; V _I or V _O = 0V to 5.5V; V _{CC} (B) = 0 V; V _{CC} (A) = 1.2V to 5.5V	-	_	±1	μΑ
Сі	Input Capacitance	DIR Input; V _I = 0V or 3.3V; Vcc(A) = Vcc(B) = 3.3V		2.2		pF
C _{I/O}	Input/Output Capacitance	A and B Port; Suspend Mode; Vo = 3.3V or 0V; Vcc(A) = Vcc(B) = 3.3V		6.0		pF

Electrical Characteristics (continued) (@T_A = +25°C.)

Comple of	Danamatan	Conditions	-40°C	to +85°C	-40°C	to +125°C	l lm it	
Symbol	Parameter	Conditions	Min	Max	Min	Max	Unit	
		Data Input						
		V _{CCI} = 1.2V	0.8V _{CCI}	_	0.8V _{CCI}	_	V	
		Vcci = 1.4V to 1.95V	0.65Vccı	_	0.65Vccı	_	V	
		V _{CCI} = 2.3V to 2.7V	1.7	_	1.7	_	V	
		V _{CCI} = 3.0V to 3.6V	2.0	_	2.0	_	V	
V _{IH}	HIGH-Level	V _{CCI} = 4.5V to 5.5V	0.7 Vcci	_	0.7 Vccı	_	V	
VIH	Input Voltage	DIR Input						
		V _{CCI} = 1.2V	0.8Vcc(A)	_	0.8Vcc(A)	_	V	
		V _{CCI} = 1.4V to 1.95V	0.65Vcc(A)	_	0.65Vcc(A)	_	V	
		V _{CCI} = 2.3V to 2.7V	1.7	_	1.7	_	V	
		V _{CCI} = 3.0V to 3.6V	2.0	_	2.0	_	V	
		V _{CCI} = 4.5V to 5.5V	0.7V _{CC} (A)	_	0.7V _{CC} (A)	_	V	
		Data Input						
		V _{CCI} = 1.2V	_	0.2Vccı	_	0.2Vccı	V	
		V _{CCI} = 1.4V to 1.95V	_	0.35V _{CCI}	_	0.35V _{CCI}	V	
		V _{CCI} = 2.3V to 2.7V	_	0.7	_	0.7	V	
		V _{CCI} = 3.0V to 3.6V	_	0.8	_	0.8	V	
V_{IL}	LOW-Level Input Voltage	V _{CCI} = 4.5V to 5.5V	_	0.3Vccı	_	0.3Vccı	V	
	remage	DIR Input						
		Vcci = 1.2V	_	0.2V _{CC} (A)	_	0.2V _{CC} (A)	V	
		V _{CCI} = 1.4V to 1.95V	_	0.35Vcc(A)	_	0.35Vcc(A)	V	
		V _{CCI} = 2.3V to 2.7V	_	0.7	_	0.7	V	
		V _{CCI} = 3.0V to 3.6V	_	0.8	_	0.8	V	



Electrical Characteristics (continued) ($@T_A = +25$ °C.)

Cumbal	Parameter	Conditions	-40°C	to +85°C	-40°C	to +125°C	l lmit
Symbol	Parameter	Conditions	Min	Max	Min	Max	Unit
		$V_{I} = V_{IH}$					
		Io = -100μA; V _{CCO} = 1.2V to 4.5V	Vcco - 0.1	_	Vcco - 0.1	_	٧
	HIGH-Level	Io = -6mA; Vcco = 1.4V	1.0	_	1.0	_	V
V_{OH}	Output Voltage	Io = -8mA; Vcco = 1.65V	1.2	_	1.2	_	V
		Io = -12mA; Vcco = 2.3V	1.9	_	1.9	_	V
		Io = -24mA; Vcco = 3.0V	2.4	_	2.4	_	V
		Io = -32mA; Vcco = 4.5V	3.8	_	3.8	_	V
		$V_I = V_{IL}$					
		I _O = 100μA; Vcco = 1.2V to 4.5V	_	0.1	_	0.1	V
	LOW-Level	Io = 6mA; Vcco = 1.4V	_	0.3	_	0.3	V
V_{OL}	Output Voltage	$I_O = 8mA; V_{CCO} = 1.65V$	_	0.45	_	0.45	V
		I _O = 12mA; V _{CCO} = 2.3V	_	0.3	_	0.3	V
		I _O = 24mA; V _{CCO} = 3.0V	_	0.55	_	0.55	V
		Io = 32mA; Vcco = 4.5V	_	0.55	_	0.55	V
lı	Input Leakage Current	DIR Input; V _I = 0V to 5.5V; V _{CCI} = 1.2V to 5.5V	_	±2	_	±10	μΑ
loz	OFF-State Output Current	A or B Port; Vo = 0V or Vcco; Vcco = 1.2V to 5.5V	_	±2	_	±10	μA
loff	Power-Off	A Port; V ₁ or V ₀ = 0V to 5.5V; V _{CC} (A) = 0V ; V _{CC} (B) = 1.2V to 5.5V	_	±2	_	±10	μA
IOFF	Leakage Current	B Port; V ₁ or V ₀ = 0V to 5.5V; V _{CC} (B) = 0V; V _{CC} (A) = 1.2V to 5.5V	_	±2	_	±10	μA
		A Port; V _I = 0V or V _{CCI} ; I _O = 0A	_		_	_	_
		Vcc(A), Vcc(B) = 1.2V to 5.5V	_	8	_	8	μA
		Vcc(A), Vcc(B) = 1.65V to 5.5V	_	3	_	3	μΑ
		$V_{CC}(A) = 5.5V ; V_{CC}(B) = 0V$	_	2	_	2	μΑ
		$V_{CC}(A) = 0V ; V_{CC}(B) = 5.5V$	-2	_	-2	_	μΑ
		B Port; $V_I = 0V$ or V_{CCI} ; $I_O = 0A$	_	_	_	_	_
Icc	Supply Current	$V_{CC}(A)$, $V_{CC}(B) = 1.2V$ to 5.5V	_	8	_	8	μΑ
		$V_{CC}(A)$, $V_{CC}(B) = 1.65V$ to 5.5V	_	3	_	3	μΑ
		$V_{CC}(A) = 5.5V ; V_{CC}(B) = 0V$	-2	_	-2	_	μΑ
		$V_{CC}(A) = 0V ; V_{CC}(B) = 5.5V$	_	2	_	2	μΑ
		A Plus B Port $(I_{CC(A)} + I_{CC(B)})$; $I_O = 0A$; $V_I = 0V$ or V_{CCI}	_	_	_	_	_
		Vcc(A), Vcc(B) = 1.2V to 5.5V	_	16	_	16	μΑ
		$V_{CC}(A)$, $V_{CC}(B) = 1.65V$ to 5.5V	_	4	_	4	μΑ
		Per Input; Vcc(A), Vcc(B) = 3.0V to 5.5V	_	_	_	_	_
ΔΙα	Additional Supply Current	A Port; A Port at Vcc(A)-0.6V; DIR at Vcc(A); B Port = Open	_	50	_	75	μA
	Guilelit	DIR Input; DIR at $V_{CC}(A)$ -0.6V; A Port at $V_{CC}(A)$ or GND; B Port = Open	_	50	_	75	μA
		B Port; B Port at Vcc(B)V -0.6V; DIR at GND; A Port = Open	_	50	_	75	μΑ



Package Characteristics (V_{CC} = 3.3V, T_A = +25°C, unless otherwise specified.)

Symbol	Parameter	Parameter Package Test Conditions		Min	Тур	Max	Unit	
0	Thermal Resistance Junction-	X2-DFN1210-8	Note 8	-	295	-	°C/W	
ΘJA to	to-Ambient	X2-DFN1410-8	Note o	_	133	_		
0	Thermal Resistance Junction-	X2-DFN1210-8	Note 8	_	280	_	°C/W	
Θ _{JC} to	to-Case	X2-DFN1410-8	Note o	_	127	_	- 'C/vv	

Note: 8. Test condition for X2- DFN1210-8 and X2- DFN1410-8: Device mounted on FR-4 substrate PCB, 2oz copper with minimum recommended pad layout.

Switching Characteristics (Vcc (A) = 1.2V, T_A = +25°C, see Figure 1)

Parameter	From	То	Vcc(B) = 1.2V	Vcc(B) = 1.5V	Vcc(B) = 1.8V	Vcc(B) = 2.5V	Vcc(B) = 3.3V	Vcc(B) = 5V	Unit
arameter	(Input)	(Output)	Тур	Тур	Тур	Тур	Тур	Тур	Oiiii
4	Α	В	10.6	8.1	7.0	5.8	5.3	5.1	20
t _{pLH}	В	Α	10.6	9.5	9.0	8.5	8.3	8.2	ns
4	Α	В	10.1	7.1	6.0	5.3	5.2	5.4	ns
t _{pHL}	В	Α	10.1	8.6	8.1	7.8	7.6	7.6	115
4	DIR	Α	9.4	9.4	9.4	9.4	9.4	9.4	20
t _{pHZ}	DIR	В	12.0	9.4	9.0	7.8	8.4	7.9	ns
4	DIR	Α	7.1	7.1	7.1	7.1	7.1	7.1	20
t _{pLZ}	DIR	В	9.5	7.8	7.7	6.9	7.6	7.0	ns
	DIR	Α	20.1	17.3	16.7	15.4	15.9	15.2	20
t _{pZH}	DIR	В	17.7	15.2	14.1	12.9	12.4	12.2	ns
4	DIR	Α	22.1	18.0	17.1	15.6	16.0	15.5	20
t _{pZL}	DIR	В	19.5	16.5	15.4	14.7	14.6	14.8	ns

Switching Characteristics (continued) (Vcc (B) = 1.2V, T_A = +25°C, see Figure 1)

Parameter	From	То	Vcc(A) = 1.2V	Vcc(A) = 1.5V	Vcc(A) = 1.8V	Vcc(A) = 2.5V	Vcc(A) = 3.3V	Vcc(A) = 5V	Unit
raranneter	(Input) (Outp		Тур	Тур	Тур	Тур	Тур	Тур	Oilit
	Α	В	10.6	9.5	9.0	8.5	8.3	8.2	20
t _{pLH}	В	Α	10.6	8.1	7.0	5.8	5.3	5.1	ns
4	Α	В	10.1	8.6	8.1	7.8	7.6	7.6	ns
tpHL	В	Α	10.1	7.1	6.0	5.3	5.2	5.4	113
4	DIR	Α	9.4	6.5	5.7	4.1	4.1	3.0	20
t _{pHZ}	DIR	В	12.0	6.1	5.4	4.6	4.3	4.0	ns
	DIR	Α	7.1	4.9	4.5	3.2	3.4	2.5	20
t _{pLZ}	DIR	В	9.5	7.3	6.6	5.9	5.7	5.6	ns
4	DIR	Α	20.1	15.4	13.6	11.7	11.0	10.7	20
t _{pZH}	DIR	В	17.7	14.4	13.5	11.7	11.7	10.7	ns
4	DIR	Α	22.1	13.2	11.4	9.9	9.5	9.4	20
t pZL	DIR	В	19.5	15.1	13.8	11.9	11.7	10.6	ns



Switching Characteristics (continued) (V_{CC} (A) = 1.5V ± 0.1V, T_A = -40°C to +85°C, see Figure 1)

Parameter	From (Input)			Vcc(B) = 1.5V ±0.1V		Vcc(B) = 1.8V ±0.15V		Vcc(B) = 2.5V ±0.2V		Vcc(B) = 3.3V ±0.3V		Vcc(B) = 5V ±0.5V	
	(mpat)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
4	Α	В	2.8	21.3	2.4	17.6	2.0	13.5	1.7	11.8	1.6	10.5	no
tpLH	В	Α	2.8	21.3	2.6	19.1	2.3	14.9	2.3	12.4	2.2	12.0	ns
4	Α	В	2.6	19.3	2.2	15.3	1.8	11.8	1.7	10.9	1.7	10.8	
tpHL	В	Α	2.6	19.3	2.4	17.3	2.3	13.2	2.2	11.3	2.3	11.0	ns
4	DIR	Α	3.0	18.7	3.0	18.7	3.0	18.7	3.0	18.7	3.0	18.7	
t _{pHZ}	DIR	В	3.5	24.8	3.5	23.6	3.0	11.0	3.3	11.3	2.8	10.3	ns
	DIR	Α	2.4	11.4	2.4	11.4	2.4	11.4	2.4	11.4	2.4	11.4	no
t _{pLZ}	DIR	В	2.8	18.3	3.0	17.2	2.5	9.4	3.0	10.1	2.5	9.4	ns
4	DIR	Α	_	39.6	_	36.3	_	24.3	_	22.5	_	21.4	
t pZH	DIR	В	_	32.7	_	29.0	_	24.9	_	23.2	_	21.9	ns
4	DIR	Α	_	44.1	_	40.9	_	24.2	_	22.6	_	21.3	no
t _{pZL}	DIR	В	_	38.0	_	34.0	_	30.5	_	29.6	_	29.5	ns

Switching Characteristics (continued) (Vcc (A) = 1.8V \pm 0.15V, TA = -40°C to +85°C, see Figure 1)

Parameter	From (Input)	To (Output)		Vcc(B) = 1.5V ±0.1V		Vcc(B) = 1.8V ±0.15V) = 2.5V 0.2V) = 3.3V).3V		3) = 5V 3.5V	Unit
	(iliput)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
4	Α	В	2.6	19.1	2.2	17.7	2.2	9.3	1.7	7.2	1.4	6.8	20
t _{pLH}	В	Α	2.4	17.6	2.2	17.7	2.3	16.0	2.1	15.5	1.9	15.1	ns
4	Α	В	2.4	17.3	2.0	14.3	1.6	8.5	1.8	7.1	1.7	7.0	20
tpHL	В	Α	2.2	15.3	2.0	14.3	2.1	12.9	2.0	12.6	1.8	12.2	ns
4	DIR	Α	2.9	17.1	2.9	17.1	2.9	17.1	2.9	17.1	2.9	17.1	20
t _{pHZ}	DIR	В	3.2	24.1	3.2	21.9	2.7	11.5	3.0	10.3	2.5	8.2	ns
4	DIR	Α	2.4	10.5	2.4	10.5	2.4	10.5	2.4	10.5	2.4	10.5	20
t _{pLZ}	DIR	В	2.5	17.6	2.6	16.0	2.2	9.2	2.7	8.4	2.4	7.1	ns
4	DIR	Α	_	35.2	_	33.7	_	25.2	_	23.9	_	22.2	no
t _{pZH}	DIR	В	_	29.6	_	28.2	_	19.8	_	17.7	_	17.3	ns
4	DIR	Α	_	39.4	_	36.2	_	24.4	_	22.9	_	20.4	20
tpZL	DIR	В	_	34.4	_	31.4	_	25.6	_	24.2	_	24.1	ns

Switching Characteristics (continued) (V_{CC} (A) = 2.5V ± 0.2V, T_A = -40°C to +85°C, see Figure 1)

Parameter	From (Input)	To (Output)		±0.1V		V _{CC} (B) = 1.8V ±0.15V) = 2.5V 0.2V) = 3.3V).3V		3) = 5V).5V	Unit
	(iliput)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
4	Α	В	2.3	17.9	2.3	16.0	1.5	8.5	1.3	6.2	1.1	4.8	20
t _{pLH}	В	Α	2.0	13.5	2.2	9.3	1.5	8.5	1.4	8.0	1.0	7.5	ns
4	Α	В	2.3	15.8	2.1	12.9	1.4	7.5	1.3	5.4	0.9	4.6	20
t _{pHL}	В	Α	1.8	11.8	1.9	8.5	1.4	7.5	1.3	7.0	0.9	6.2	ns
4	DIR	Α	2.1	8.1	2.1	8.1	2.1	8.1	2.1	8.1	2.1	8.1	20
t _{pHZ}	DIR	В	3.0	22.5	3.0	21.4	2.5	11.0	2.8	9.3	2.3	6.9	ns
4	DIR	Α	1.7	5.8	1.7	5.8	1.7	5.8	1.7	5.8	1.7	5.8	ns
t _{pLZ}	DIR	В	2.3	14.6	2.5	13.2	2.0	9.0	2.5	8.4	1.8	5.8	115
4	DIR	Α	_	28.1	_	22.5	_	17.5	_	16.4	_	13.3	20
tpZH	DIR	В	_	23.7	_	21.8	_	14.3	_	12.0	_	10.6	ns
4	DIR	Α	-	34.3	_	29.9		18.5	_	16.3	_	13.1	20
t _{pZL}	DIR	В	_	23.9	_	21.0	_	15.6	_	13.5	_	12.7	ns



Switching Characteristics (continued) (V_{CC} (A) = 3.3V ± 0.3V, T_A = -40°C to +85°C, see Figure 1)

Parameter	From (Input)	To (Output)		Vcc(B) = 1.5V ±0.1V		Vcc(B) = 1.8V ±0.15V) = 2.5V 0.2V	, ,) = 3.3V).3V	,	s) = 5V .5V	Unit
	(iliput)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
4	Α	В	2.3	17.1	2.1	15.5	1.4	8.0	0.8	5.6	0.7	4.4	ns
t _{pLH}	В	Α	1.7	11.8	1.7	7.2	1.3	6.2	0.7	5.6	0.6	5.4	115
4	Α	В	2.2	15.6	2.0	12.6	1.3	7.0	0.8	5.0	0.7	4.0	20
t _{pHL}	В	Α	1.7	10.9	1.8	7.1	1.3	5.4	0.8	5.0	0.7	4.5	ns
4	DIR	Α	2.3	7.3	2.3	7.3	2.3	7.3	2.3	7.3	2.7	7.3	20
t _{pHZ}	DIR	В	2.9	18.0	2.9	16.5	2.3	10.1	2.7	8.6	2.2	6.3	ns
.	DIR	Α	2.0	5.6	2.0	5.6	2.0	5.6	2.0	5.6	2.0	5.6	
t _{pLZ}	DIR	В	2.3	13.6	2.4	12.5	1.9	7.8	2.3	7.1	1.7	4.9	ns
4	DIR	Α	_	25.4	_	19.7	_	14.0	_	12.7	_	10.3	
t pZH	DIR	В	_	22.7	_	21.1	_	13.6	_	11.2	_	10.0	ns
	DIR	Α	_	28.9	_	23.6	_	15.5	_	13.6	_	10.8	20
t _{pZL}	DIR	В	_	22.9	_	19.9	_	14.3	_	12.3	_	11.3	ns

Switching Characteristics (continued) (V_{CC} (A) = 5.0V ± 0.5V, T_A = -40°C to +85°C, see Figure 1)

Parameter	From (Input)	To (Output)		= 1.5V .1V) = 1.8V .15V) = 2.5V 0.2V) = 3.3V).3V		3) = 5V 3.5V	Unit
	(iliput)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
4	Α	В	2.2	16.6	1.9	15.1	1.0	7.5	0.7	5.4	0.5	3.9	20
t _р LН	В	Α	1.6	10.5	1.4	6.8	1.0	4.8	0.7	4.4	0.5	3.9	ns
4	Α	В	2.3	15.3	1.8	12.2	1.0	6.2	0.7	4.5	0.5	3.5	20
t _{pHL}	В	Α	1.7	10.8	1.7	7.0	0.9	4.6	0.7	4.0	0.5	3.5	ns
4	DIR	Α	1.7	5.4	1.7	5.4	1.7	5.4	1.7	5.4	1.7	5.4	ns
t _{pHZ}	DIR	В	2.9	17.3	2.9	16.1	2.3	9.7	2.7	8.0	2.5	5.7	115
4	DIR	Α	1.4	3.7	1.4	3.7	1.3	3.7	1.0	3.7	0.9	3.7	ns
t _{pLZ}	DIR	В	2.3	13.1	2.4	12.1	1.9	7.4	2.3	7.0	1.8	4.5	115
4	DIR	Α	_	23.6	_	18.9	_	12.2	_	11.4	_	8.4	20
t pZH	DIR	В	_	20.3	_	18.8	_	11.2	_	9.1	_	7.6	ns
4	DIR	Α	_	28.1	_	23.1	_	14.3	_	12.0	_	9.2	20
t _{pZL}	DIR	В	_	20.7	_	17.6	_	11.6	_	9.9	_	8.9	ns

Switching Characteristics (continued) (V_{CC} (A) = 1.5V ± 0.1V, T_A = -40°C to +125°C, see Figure 1)

Parameter	From (Input)	To (Output)	V _{CC} (B) = 1.5V ±0.1V			V _{CC} (B) = 1.8V ±0.15V) = 2.5V 0.2V) = 3.3V).3V		3) = 5V).5V	Unit
	(Iliput)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
4	Α	В	2.5	23.5	2.1	19.4	1.8	14.9	1.5	13.0	1.4	11.6	ns
t _{pLH}	В	Α	2.5	23.5	2.3	21.1	2.0	16.4	2.0	13.7	1.9	13.2	ns
	Α	В	2.3	21.3	1.9	16.9	1.6	13.0	1.5	12.0	1.5	11.9	20
t _{pHL}	В	Α	2.3	21.3	2.1	19.1	2.0	14.6	1.9	12.5	2.0	12.1	ns
4	DIR	Α	2.7	20.6	2.7	20.6	2.7	20.6	2.7	20.6	2.7	20.6	20
t _{pHZ}	DIR	В	3.1	27.3	3.1	26.0	2.7	12.1	2.9	12.5	2.5	11.4	ns
	DIR	Α	2.1	12.6	2.1	12.6	2.1	12.6	2.1	12.6	2.1	12.6	
t _{pLZ}	DIR	В	2.5	20.2	2.7	19.0	2.2	10.4	2.7	11.2	2.2	10.4	ns
4	DIR	Α	_	43.7	_	40.1	_	26.8	_	24.9	_	23.6	20
t _р zн	DIR	В	_	36.1	_	32.0	_	27.5	_	25.6	_	24.2	ns
4	DIR	Α	_	48.6	_	45.1	_	26.7	_	25.0	_	23.5	no
t _{pZL}	DIR	В	_	41.9	_	37.5	_	33.6	_	32.6	_	32.5	ns



Switching Characteristics (continued) (V_{CC} (A) = 1.8V \pm 0.15V, T_A = -40°C to +125°C, see Figure 1)

Parameter	From (Input)	To (Output)		Vcc(B) = 1.5V ±0.1V		Vcc(B) = 1.8V ±0.15V) = 2.5V 0.2V) = 3.3V).3V		3) = 5V 3.5V	Unit
	(iliput)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
4	Α	В	2.3	21.1	1.9	19.5	1.9	10.3	1.5	8.0	1.2	7.5	ns
t _{pLH}	В	Α	2.1	19.4	1.9	19.5	2.0	17.6	1.8	17.1	1.7	16.7	115
	Α	В	2.1	19.1	1.8	15.8	1.4	9.4	1.6	7.9	1.5	7.7	20
t _{pHL}	В	Α	1.9	16.9	1.8	15.8	1.8	14.2	1.8	13.9	1.6	13.5	ns
	DIR	Α	2.6	18.9	2.6	18.9	2.6	18.9	2.6	18.9	2.6	18.9	
t _{pHZ}	DIR	В	2.8	26.6	2.8	24.1	2.4	12.7	2.7	11.4	2.2	9.1	ns
	DIR	Α	2.1	11.6	2.1	11.6	2.1	11.6	2.1	11.6	2.1	11.6	
t _{pLZ}	DIR	В	2.2	19.4	2.3	17.6	1.9	10.2	2.4	9.3	2.1	7.9	ns
	DIR	Α	_	38.8	_	37.1	_	27.8	_	26.4	_	24.6	
t pZH	DIR	В	_	32.7	_	31.1	_	21.9	_	19.6	_	19.1	ns
	DIR	Α	_	43.5	_	39.9	_	26.9	_	25.3	_	22.6	20
t _{pZL}	DIR	В	_	38.0	_	34.7	_	28.3	_	26.8	_	26.6	ns

Switching Characteristics (continued) (Vcc (A) = 2.5V \pm 0.2V, TA = -40°C to +125°C, see Figure 1)

Parameter	From (Input)	To (Output)		Vcc(B) = 1.5V ±0.1V		Vcc(B) = 1.8V ±0.15V) = 2.5V 0.2V) = 3.3V).3V		3) = 5V 3.5V	Unit
	(iliput)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
4	Α	В	2.0	19.7	2.0	17.6	1.3	9.4	1.1	6.9	0.9	5.3	ns
t _{pLH}	В	Α	1.8	14.9	1.9	10.3	1.3	9.4	1.2	8.8	0.9	8.3	TIS
4	Α	В	2.0	17.4	1.8	14.2	1.2	8.3	1.1	6.0	0.8	5.1	
tpHL	В	Α	1.6	13.0	1.7	9.4	1.2	8.3	1.1	7.7	0.8	6.9	ns
4	DIR	Α	1.8	9.0	1.8	9.0	1.8	9.0	1.8	9.0	1.8	9.0	
t _{pHZ}	DIR	В	2.7	24.8	2.7	23.6	2.2	12.1	2.5	10.3	2.0	7.6	ns
4	DIR	Α	1.5	6.4	1.5	6.4	1.5	6.4	1.5	6.4	1.5	6.4	ns
t _{pLZ}	DIR	В	2.0	16.1	2.2	14.6	1.8	9.9	2.2	9.3	1.6	6.4	115
	DIR	Α	_	31.0	_	24.9	_	19.3	_	18.1	_	14.7	
tpZH	DIR	В	_	26.1	_	24.0	_	15.8	_	13.3	_	11.7	ns
4	DIR	Α	_	37.8	_	33.0	_	20.4	_	18.0	_	14.5	no
t _{pZL}	DIR	В	_	26.4	_	23.2	_	17.3	_	15.0	_	14.1	ns

Switching Characteristics (continued) (V_{CC} (A) = 3.3V ± 0.3V, T_A = -40°C to +125°C, see Figure 1)

Parameter	From (Input)	To (Output)		= 1.5V .1V		V _{CC} (B) = 1.8V ±0.15V) = 2.5V 0.2V) = 3.3V).3V		3) = 5V 3.5V	Unit
	(iliput)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
4	Α	В	2.0	18.9	1.8	17.1	1.2	8.8	0.7	6.2	0.6	4.9	ns
t _{pLH}	В	Α	1.5	13.0	1.5	8.0	1.1	6.9	0.6	6.2	0.5	6.0	115
4	Α	В	1.9	17.2	1.8	13.9	1.1	7.7	0.7	5.5	0.6	4.4	ns
t _{pHL}	В	Α	1.5	12.0	1.6	7.9	1.1	6.0	0.7	5.5	0.6	5.0	115
4	DIR	Α	2.0	8.1	2.0	8.1	2.0	8.1	2.0	8.1	2.4	8.1	20
t _{pHZ}	DIR	В	2.6	19.8	2.6	18.2	2.0	11.2	2.4	9.5	1.9	7.0	ns
4	DIR	Α	1.8	6.2	1.8	6.2	1.8	6.2	1.8	6.2	1.8	6.2	20
t _{pLZ}	DIR	В	2.0	15.0	2.1	13.8	1.7	8.6	2.0	7.9	1.5	5.4	ns
4	DIR	Α	_	28.0	_	21.8	_	15.5	_	14.1	_	11.4	20
t pZH	DIR	В	_	25.1	_	23.3	_	15.0	_	12.4	_	11.1	ns
	DIR	Α	_	31.8	_	26.1	_	17.2	_	15.0	_	12.0	20
t pZL	DIR	В	_	25.3	_	22.0	_	15.8	_	13.6	_	12.5	ns



Switching Characteristics (continued) (V_{CC} (A) = 5.0V \pm 0.5V, T_{A} = -40°C to +125°C, see Figure 1)

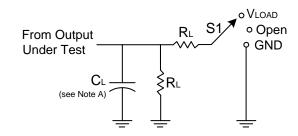
Parameter	From (Input)	To (Output)	output) ±0.1V			Vcc(B) = 1.8V ±0.15V) = 2.5V 0.2V) = 3.3V).3V		3) = 5V).5V	Unit
	(Iliput)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
4	Α	В	1.9	18.3	1.7	16.7	0.9	8.3	0.6	6.0	0.4	4.3	ns
t _{pLH}	В	Α	1.4	11.6	1.2	7.5	0.9	5.3	0.6	4.9	0.4	4.3	115
4	Α	В	2.0	16.9	1.6	13.5	0.9	6.9	0.6	5.0	0.4	3.9	
t _{pHL}	В	Α	1.5	11.9	1.5	7.7	0.8	5.1	0.6	4.4	0.4	3.9	ns
	DIR	Α	1.5	6.0	1.5	6.0	1.5	6.0	1.5	6.0	1.5	6.0	
t _{pHZ}	DIR	В	2.6	19.1	2.6	17.8	2.0	10.7	2.4	8.8	2.2	6.3	ns
	DIR	Α	1.2	4.1	1.2	4.1	1.1	4.1	0.9	4.1	0.8	4.1	
t _{pLZ}	DIR	В	2.0	14.5	2.1	13.4	1.7	8.2	2.0	7.7	1.6	5.0	ns
	DIR	Α	_	26.1	_	20.9	_	13.5	_	12.6	_	9.3	
tpZH	DIR	В	_	22.4	_	20.8	_	12.4	_	10.1	_	8.4	ns
	DIR	Α	_	31.0	_	25.5	_	15.8	_	13.2	_	10.2	
t _{pZL}	DIR	В	_	22.9	_	19.5	_	12.9	_	11.0	_	9.9	ns

Operating Characteristics (T_A = +25°C, unless otherwise specified.)

	Parameter sipation Capacitance	Test Conditions	Vcc(A) = Vcc(B) = 1.8V Typ	Vcc(A) = Vcc(B) = 2.5V Typ	Vcc(A) = Vcc(B) = 3.3V Typ	Vcc(A) = Vcc(B) = 5V Typ	Unit
	A- Input, B- Output	$C_L = 0pF$	3	4	4	4	
C _{pd} (A)	B- Input, A- Output	f = 10MHz $t_R = t_F = 1ns$	18	19	20	21	pF
0 (5)	A- Input, B- Output	C _L = 0pF	18	19	20	21	1
C _{pd} (B)	C _{pd} (B) B- Input, A- Output	f = 10 MHz $t_R = t_F = 1 \text{ ns}$	3	4	4	4	pF

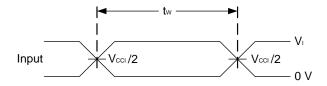


Parameter Measurement Information

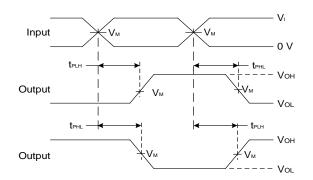


TEST	S1
tpLH/tpHL	Open
t _{PLZ} /t _{PZL}	Vload
tpHZ/tpZH	GND

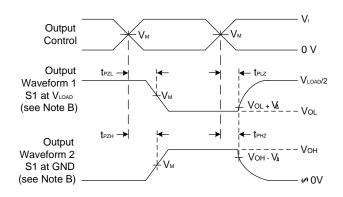
V	Inp	outs	Vice	V		D.	V/A
Vcc	Vı	tr/tf	Vм	VLOAD	C∟	R∟	V Δ
1.8V±0.15V	Vccı	≤2ns	Vcco/2	2 X Vcco	15pF	2ΚΩ	0.15V
2.5V±0.2V	Vcc	≤2ns	V _{CCO} /2	2 X V _{CCO}	15pF	2ΚΩ	0.15V
3.3V±0.3V	3V	≤2.5ns	Vcco/2	2 X Vcco	15pF	2ΚΩ	0.3V
5V±0.5V	Vcc	≤2.5ns	V _{CCO} /2	2 X V _{CCO}	15pF	2ΚΩ	0.3V



Voltage Waveform Pulse Duration



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs



Voltage Waveform Enable and Disable Times Low and High Level Enabling

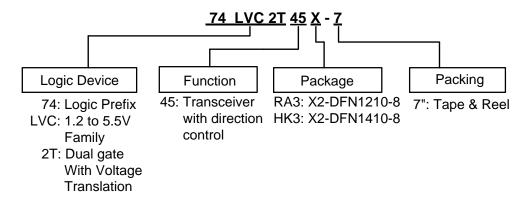
Figure 1 Load Circuit and Voltage Waveforms

Notes:

- 9. Includes test lead and test apparatus capacitance.
- 10. Waveform 1 is for an output with input set up as a low and device coming out or into 3-state via DIR control. Waveform 2 is for an output with input set up as a high and device coming out or into 3-state via DIR control.
- 11. All pulses are supplied at pulse repetition rate ≤ 10 MHz.
- 12. t_{PLZ} and t_{PHZ} are the same as $t_{dis.}$
- 13. t_{PZL} and t_{PZH} are the same as t_{EN}.
- 14. t_{PLH} and t_{PHL} are the same as t_{PD} .
- 15. V_{CCI} is the V_{CC} associated with the input.
- 16. V_{CCO} is the V_{CC} associated with the output.



Ordering Information



Part Number	Package Code Packaging 7		7" Tape and	and Reel (Note 7)	
Fait Number	Number Package Code Packaging	Packaging	Quantity	Part Number Suffix	
74LVC2T45RA3-7	RA3	X2-DFN1210-8	5000/Tape & Reel	-7	
74LVC2T45HK3-7	HK3	X2-DFN1410-8	5000/Tape & Reel	-7	

Note: 17. The taping orientation is located on our website at http://www.diodes.com/package-outlines.html.

Marking Information

(1) X2-DFN1210-8

(Top View)

<u>XX</u> XX: Identification Code

Y: Year: 0~9

<u>W</u>: Week: A~Z: 1~26 week; a~z: 27~52 week; z represents

52 and 53 week X: Internal Code

Part Number	Package	Identification Code
74LVC2T45RA3-7	X2-DFN1210-8	4A

(2) X2-DFN1410-8

(Top View)



XX: Identification Code

<u>Y</u> : Year : 0~9

<u>W</u>: Week: A~Z: 1~26 week; a~z: 27~52 week; z represents

52 and 53 week

X: Internal Code

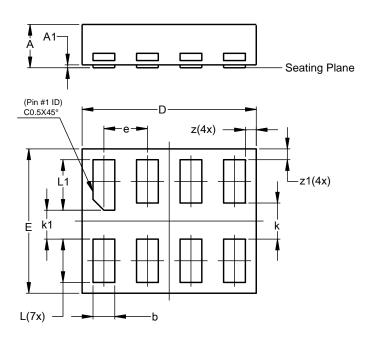
Part Number	Package	Identification Code
74LVC2T45HK3-7	X2-DFN1410-8	4B



Package Outline Dimensions

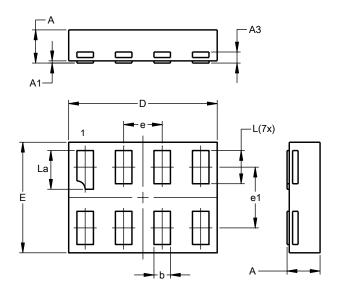
Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1210-8



X2-DFN1210-8			
Dim	Min	Max	Тур
Α	-	0.35	0.30
A1	0	0.03	0.02
b	0.10	0.20	0.15
D	1.15	1.25	1.20
Е	0.95	1.05	1.00
е	-	-	0.30
k	-	-	0.25
k1	-	-	0.20
١	0.25	0.35	0.30
L1	0.30	0.40	0.35
Z	0.050	0.100	0.075
z1	0.050	0.100	0.075
All Dimensions in mm			

X2-DFN1410-8



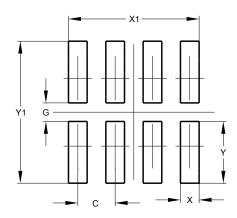
X2-DFN1410-8			
Dim	Min	Max	Тур
Α	0.30	0.35	0.33
A1	0.00	0.03	0.02
А3	-		0.10
b	0.12	0.20	0.15
D	1.30	1.40	1.35
Е	0.95	1.05	1.00
е			0.35
e1			0.55
L	0.27	0.35	0.30
L1	0.32	0.40	0.35
All Dimensions in mm			



Suggested Pad Layout

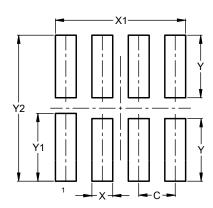
Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1210-8



Dimensions	Value (in mm)	
С	0.300	
G	0.150	
Х	0.150	
X1	1.050	
Y	0.500	
Y1	1.150	

X2-DFN1410-8



Dimensions	Value	
Dillicipions	(in mm)	
С	0.350	
Х	0.200	
X1	1.250	
Y	0.600	
Y1	0.650	
Y2	1.400	

Mechanical Data

X2-DFN1210-8

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu Nickel Palladium Gold, Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.002 grams (Approximate)

X2-DFN1410-8

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu Nickel Palladium Gold, Solderable per MIL-STD-202, Method 208 (4)
- Weight: 0.002 grams (Approximate)



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